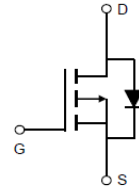


The ZM350P10I combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

Trench technology  
 $R_{DS(ON)}$  to minimize conductive loss

nd Synchronous Rectifier

### Product Summary



$V_{DS} = -100V$

$R_{DS(ON)} = 40m\Omega$

$I_D = -30A$



TO-251

Part NO.	ZM350P10I
Marking	ZM350P10
Packing Information	TUBE
Basic ordering unit (pcs)	900

$T_c = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_{D@TC=25}$	-30	A
	$I_{D@TC=75}$	-23	A
	$I_{D@TC=100}$	-19	A
Pulsed Drain Current	$I_{DM}$	-90	A
Total Power Dissipation	$P_D@TC=25$	55	W
Total Power Dissipation	$P_D@TA=25$	2.5	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	$E_{AS}$	160	mJ



Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate

Fig.1 Gate-Charge Characteristics

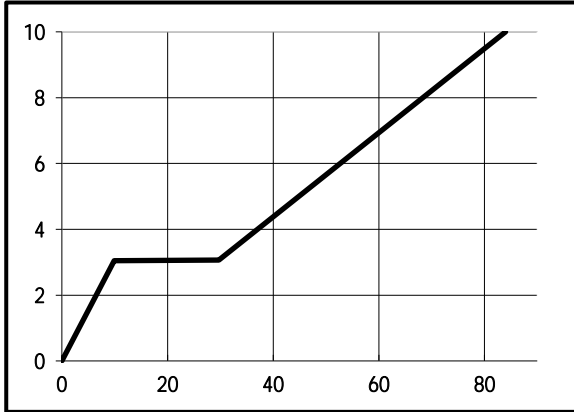


Fig.2 Capacitance Characteristics

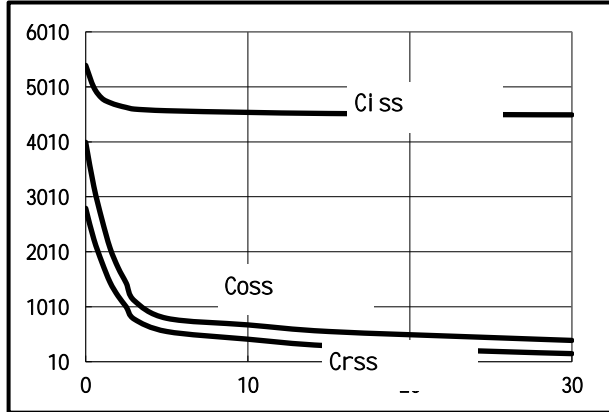


Fig.3 Power Dissipation

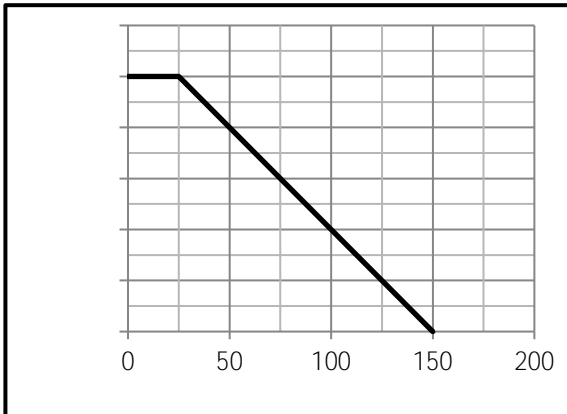


Fig.4 Typical output Characteristics

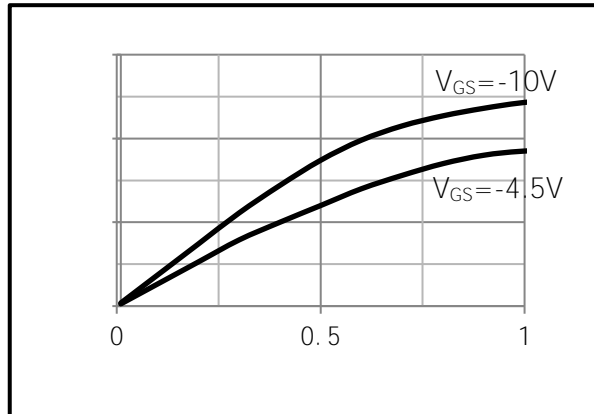


Fig.5 Threshold Voltage V.S Junction Temperature

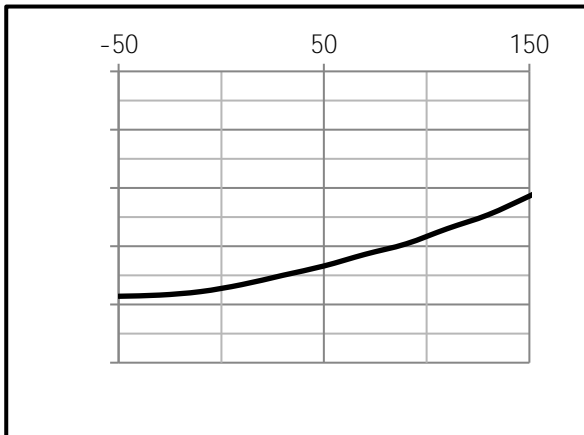


Fig.6 Resistance V.S Drain Current

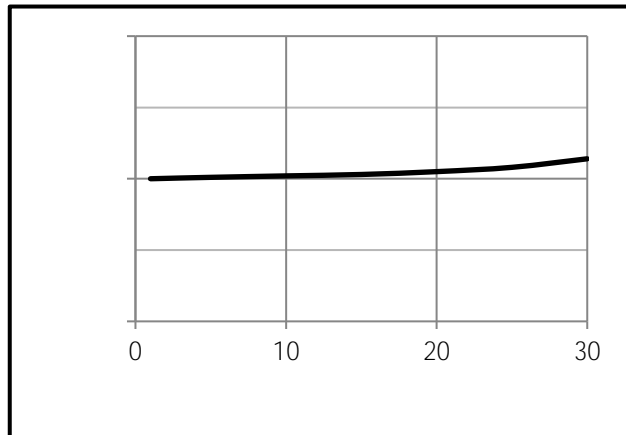


Fig.7 On-Resistance VS Gate Source Voltage

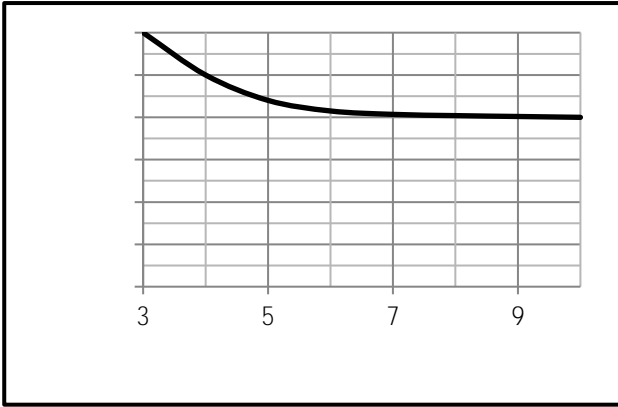


Fig.8 On-Resistance V.S Junction Temperature

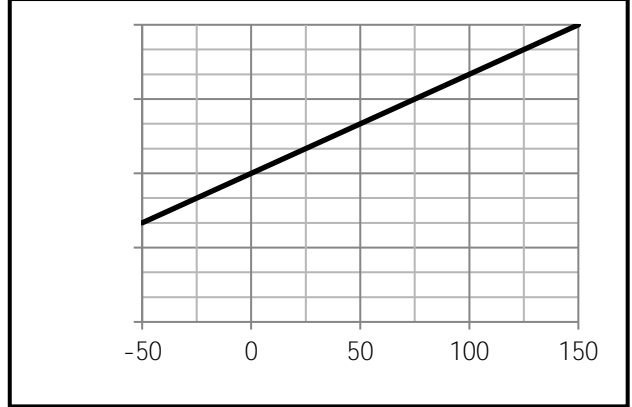


Fig.9 Switching Time Measurement Circuit

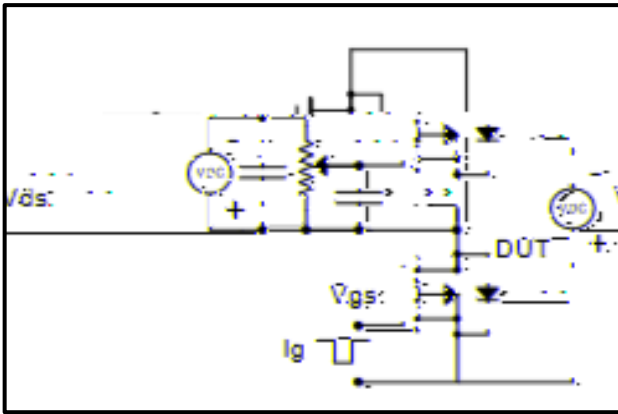


Fig.10 Gate Charge Waveform

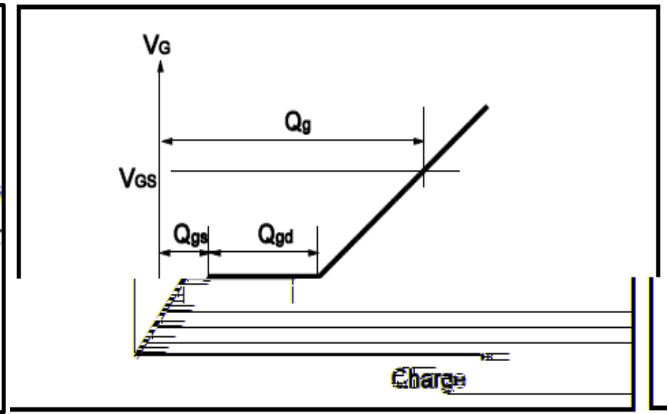


Fig.11 Switching Time Measurement Circuit

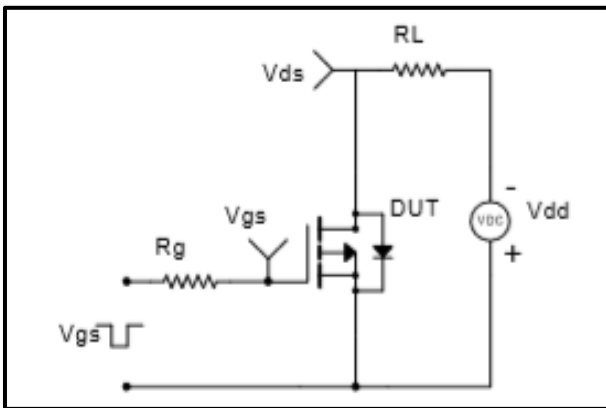


Fig.12 Gate Charge Waveform

